

NPN RF TRANSISTOR

DESCRIPTION:

The **ASI MSC80278** is a Silicon NPN Microwave Transistor Supplied in a Common Emitter Package, Designed for linear Applications.

FEATURES:

- Emitter Ballasted
- Gold Metallization
- Hermetically sealed Package

MAXIMUM RATINGS

I_C	300 mA
V_{CEO}	20 V
P_{DISS}	5.0 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	$35^\circ C/W$

PACKAGE 250 2L FLG

DIM	MILLIMETER	TOL	INCHES	TOL
A	20.32	.13	.800	.005
B	14.27	.13	.562	.005
C	18.03	MIN	.710	MIN
D	5.84	.13	.230	.005
E	3.05	.13	.120	.005
F	1.27 x 45°	.13	.005x45°	.005
G	5.84	.13	.230	.005
H	4.57	REF	.180	REF
I	0.13	.02	.005	.001
J	3.30	.13	.130	.005
K	1.52	.13	.060	.005
M	1.27	.13	.050	.005
N	3.30 DIA	.13	.130 DIA	.005

1 = Collector 2 = Emitter
 3 = Base

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{CBO}	$I_C = 1.0$ mA	50			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CEO}	$V_{CE} = 18$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		120	---
G_P	$P_{out} = 28$ dBm $f = 2.0$ GHz			1.0	dB
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			3.0	pF